Examiner's First Action dated May 10,2002, together with a one month time extension to extend the due date to and including September 10, 2002.

**In the Specification**

Page 1, lines 17-22, replace with the following:

A1

Another main driver in semiconductor technology is the trend toward smaller device structures. Metal oxide semiconductor field effect transistors (MOSFET) with submicron gate dimensions of the order of 100 to 250 nm are being developed. Performance improvements for these small gate dimension devices are generally obtained by changing the physical structure and materials used in the device and by inventing new processes or improving an existing process for making the devices.

Page 5, lines 21-33, substitute the following:

A2

Referring to FIG. 2A, an amorphous silicon (α-Si ) layer 200 is formed on top of a crystalline silicon substrate (c-Si) 210. Laser beam 230 irradiates the top surface 202 of the amorphous silicon layer 200. Laser beam 230 is pulsed radiation generated by a Neodymium YAG laser and has a wavelength of 532 nanometers. The heat from the laser beam 230 melts a first thin layer 220 of the amorphous silicon 200 near the top surface 202. In one example the energy fluence is 0.4 $J/cm^2$ and is delivered in a series of 3 to 10 pulses having a temporal width of 16 nanoseconds at a repetition rate preferably between 3 Hz and 10 Hz. Between pulses of the laser beam 230, the molten layer 220 is allowed to cool to room temperature causing explosive recrystallization (XRC) of the amorphous silicon 200. XRC is well known in the art and is described in US Patent 6,274,488 and in a published paper "Explosive Crystallization in Amorphous Si Initiated by Long Pulse Width Laser Irradiation", P.S. Peercy, J.Y. Tsao, S. R. Stiffler and Michael O. Thompson, Appl. Phys. Lett. 54 (3), 18 January 1988.

Page 8, lines 24-26, replace with the following:

A3

Laser beam 230 is pulsed radiation generated by a Neodymium YAG laser and